In the claims:

Please amend the claims as follows:

1. (Currently Amended) A semiconductor device comprising at least one thin film transistor over a substrate, said thin film transistor comprising:

a conductive layer comprising aluminum;

an insulating film formed on said conductive layer;

a contact hole formed through said insulating film;

a wiring electrically connected with said conductive layer in said contact hole; and

an alloy comprising at least one selected from the group consisting of ~~Sn,~~ Ga~~, Zn, Pb, In,~~ and Sb existing at least in said contact hole and ~~at a boundary~~ between said conductive layer and said wiring ~~and a vicinity thereof~~.

2. (Original) The semiconductor device of claim 1 wherein said wiring comprises aluminum.

3. (Canceled)

4. (Original) The semiconductor device of claim 1 wherein said semiconductor device is an active matrix type EL display device.

5-8. (Canceled)

9. (Currently Amended) A semiconductor device comprising at least one thin film transistor over a substrate, said thin film transistor comprising:

two conductive films comprising aluminum electrically connected with each other in a contact hole opened in an insulating film; and

an alloy comprising at least one selected from the group consisting of ~~Sn,~~ Ga~~, Zn, Pb, In,~~ and Sb existing at least in said contact hole and ~~at a boundary~~ between said two conductive films ~~and a vicinity thereof~~.

10. (Canceled)

11. (Original) The semiconductor device of claim 9 wherein said semiconductor device is an active matrix type EL display device.

12-14. (Canceled)

15. (Currently Amended) A semiconductor device comprising at least one thin film transistor over a substrate, said thin film transistor comprising:

a wiring electrode comprising aluminum which is electrically connected to at least a part of said semiconductor device through a contact hole formed through an interlayer insulating film; and

an alloy comprising at least one selected from the group consisting of ~~Sn,~~ Ga~~, Zn, Pb, In,~~ and Sb contained in the wiring electrode and existing at least in said contact hole and ~~at a boundary~~ between said wiring electrode and the part of said semiconductor device which one renders the wiring electrode flowable at 450 °C or less.

16-18. (Canceled)

19. (Original) The semiconductor device of claim 15 wherein said semiconductor device is an active matrix type EL display device.

20. (Currently Amended) A semiconductor device comprising:

at least one thin film transistor formed over a substrate, said thin film transistor comprising at least a semiconductor region, a gate electrode, and a gate insulating film interposed therebetween;

an interlayer insulating film formed over said thin film transistor;

a contact hole formed through said interlayer insulating film;

a wiring electrically connected with said semiconductor region in said contact hole; and

an alloy comprising at least one selected from the group consisting of ~~Sn,~~ Ga~~, Zn, Pb, In,~~ and Sb existing at least in said contact hole and ~~at a boundary~~ between said semiconductor region and said wiring ~~and a vicinity thereof~~.

21. (Original) The semiconductor device of claim 20 wherein said wiring comprises aluminum.

22. (Canceled)

23. (Original) The semiconductor device of claim 20 wherein said semiconductor device is an active matrix type EL display device.

24-27. (Canceled)